

# Schottky Barrier Diode

## RB481K

### ●Applications

Low current rectification

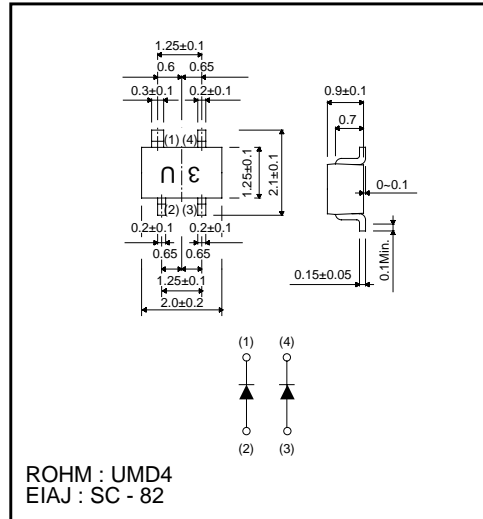
### ●Features

- 1) Compact size.
- 2) High reliability.
- 3) Extremely low forward voltage.
- 4) This is a composite component and is ideal for reducing the number of components used.

### ●Construction

Silicon epitaxial planar

### ●External dimensions (Units: mm)



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	$V_{RM}$	30	V
DC reverse voltage	$V_R$	30	V
Mean rectifying current	$I_O$	0.2	A
Peak forward surge current*	$I_{FSM}$	1	A
Junction temperature	$T_J$	125	°C
Storage temperature	$T_{stg}$	-40~+125	°C

\* 60 Hz for 1  $\mu$ s

### ●Electrical characteristics (Ta=25°C unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{F1}$	–	0.18	0.28	V	$I_F=1\text{mA}$
	$V_{F2}$	–	0.25	0.33	V	$I_F=10\text{mA}$
	$V_{F3}$	–	0.34	0.43	V	$I_F=100\text{mA}$
	$V_{F4}$	–	0.40	0.50	V	$I_F=200\text{mA}$
Reverse current	$I_R$	–	3.6	30	$\mu\text{A}$	$V_R=10\text{V}$

Diodes

● Electrical characteristic curves (Ta=25°C)

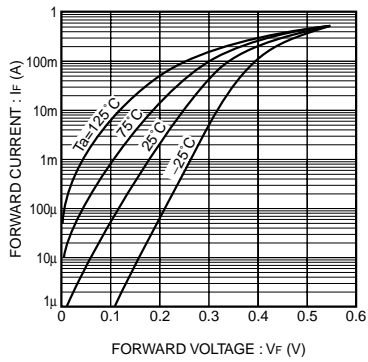


Fig. 1 Forward temperature characteristic

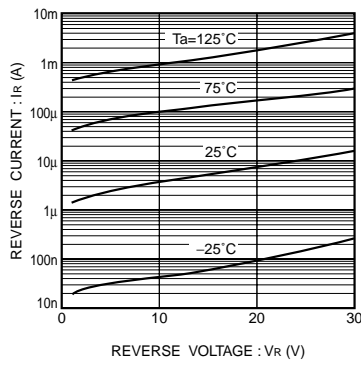


Fig. 2 Reverse temperature characteristic

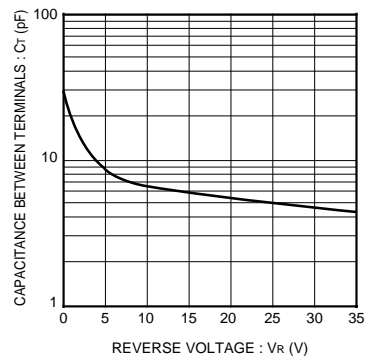


Fig. 3 Capacitance between terminals characteristic